

# Eugene Yakimov

## List of Publications by Citations

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312  
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#	Paper	IF	Citations
312	Point defect induced degradation of electrical properties of Ga <sub>2</sub> O <sub>3</sub> by 10 MeV proton damage. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 032107	3.4	72
311	What is the real value of diffusion length in GaN?. <i>Journal of Alloys and Compounds</i> , <b>2015</b> , 627, 344-351	5.7	58
310	EBIC measurements of small diffusion length in semiconductor structures. <i>Semiconductors</i> , <b>2007</b> , 41, 411-413	0.7	46
309	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated $\beta$ -Ga <sub>2</sub> O <sub>3</sub> . <i>Applied Physics Letters</i> , <b>2018</b> , 113, 092102	3.4	46
308	Spatial variations of doping and lifetime in epitaxial laterally overgrown GaN. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 152114	3.4	42
307	On the real structure of monocrystalline silicon near dislocation slip planes. <i>Physica Status Solidi A</i> , <b>1981</b> , 68, 53-60		42
306	The effect of thermal treatment on the electrical activity and mobility of dislocations in Si. <i>Physica Status Solidi A</i> , <b>1980</b> , 60, 341-349		39
305	Diffusion length of non-equilibrium minority charge carriers in $\beta$ -Ga <sub>2</sub> O <sub>3</sub> measured by electron beam induced current. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 185704	2.5	37
304	Donor nonuniformity in undoped and Si doped n-GaN prepared by epitaxial lateral overgrowth. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 042118	3.4	37
303	Effects of laterally overgrown n-GaN thickness on defect and deep level concentrations. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2008</b> , 26, 990		36
302	Electron-beam-induced-current study of defects in GaN; experiments and simulation. <i>Journal of Physics Condensed Matter</i> , <b>2002</b> , 14, 13069-13077	1.8	35
301	Nonradiative recombination dynamics in InGaN/GaN LED defect system. <i>Superlattices and Microstructures</i> , <b>2009</b> , 45, 301-307	2.8	33
300	Hydrogen plasma treatment of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> : Changes in electrical properties and deep trap spectra. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 032101	3.4	29
299	Annealing effect on the electrical activity of extended defects in plastically deformed p-Si with low dislocation density. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2005</b> , 202, 896-900	1.6	29
298	Neutron Radiation Effects in Epitaxially Laterally Overgrown GaN Films. <i>Journal of Electronic Materials</i> , <b>2007</b> , 36, 1320-1325	1.9	28
297	Recombination properties of dislocation slip planes. <i>Physica Status Solidi A</i> , <b>1986</b> , 95, 173-177		27
296	Electrical Properties, Deep Trap and Luminescence Spectra in Semi-Insulating, Czochochalski $\beta$ -Ga <sub>2</sub> O <sub>3</sub> (Mg). <i>ECS Journal of Solid State Science and Technology</i> , <b>2019</b> , 8, Q3019-Q3023	2	25

295	Defects at the surface of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> produced by Ar plasma exposure. <i>APL Materials</i> , <b>2019</b> , 7, 061102	5.7	25
294	Temperature dependence of dislocation efficiency as sinks for self-interstitials in silicon as measured by gold diffusion. <i>Journal of Applied Physics</i> , <b>1995</b> , 78, 1495-1499	2.5	25
293	On the nature of hydrogen-related centers in p-type irradiated silicon. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 308-310, 210-212	2.8	24
292	Deep traps determining the non-radiative lifetime and defect band yellow luminescence in n-GaN. <i>Journal of Alloys and Compounds</i> , <b>2016</b> , 686, 1044-1052	5.7	24
291	Contribution of the disturbed dislocation slip planes to the electrical properties of plastically deformed silicon. <i>Physica B: Condensed Matter</i> , <b>2003</b> , 340-342, 1005-1008	2.8	23
290	Electrical, luminescent, and deep trap properties of Si doped n-GaN grown by pendeo epitaxy. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 015103	2.5	23
289	Studies of deep level centers determining the diffusion length in epitaxial layers and crystals of undoped n-GaN. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 205109	2.5	23
288	Deep trap spectra of Sn-doped $\beta$ -Ga <sub>2</sub> O <sub>3</sub> grown by halide vapor phase epitaxy on sapphire. <i>APL Materials</i> , <b>2019</b> , 7, 051103	5.7	22
287	Defects responsible for lifetime degradation in electron irradiated n-GaN grown by hydride vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 112102	3.4	21
286	Betavoltaic battery performance: Comparison of modeling and experiment. <i>Applied Radiation and Isotopes</i> , <b>2018</b> , 137, 184-189	1.7	21
285	Anomalous electrical properties of dislocation slip plane in Si. <i>EPJ Applied Physics</i> , <b>2004</b> , 27, 349-351	1.1	21
284	Recombination properties of dislocations in GaN. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 161543	2.5	21
283	EBIC Investigastion of the Electrical Activity of Dislocations with Different Impurity Atmospheres in Si. <i>Physica Status Solidi A</i> , <b>1990</b> , 122, 121-128		20
282	Electrical Properties, Deep Levels and Luminescence Related to Fe in Bulk Semi-Insulating $\beta$ -Ga <sub>2</sub> O <sub>3</sub> Doped with Fe. <i>ECS Journal of Solid State Science and Technology</i> , <b>2019</b> , 8, Q3091-Q3096	2	19
281	Movement of basal plane dislocations in GaN during electron beam irradiation. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 132101	3.4	19
280	Point defects controlling non-radiative recombination in GaN blue light emitting diodes: Insights from radiation damage experiments. <i>Journal of Applied Physics</i> , <b>2017</b> , 122, 115704	2.5	19
279	Hydrogen penetration into silicon during wet-chemical etching. <i>Microelectronic Engineering</i> , <b>2003</b> , 66, 320-326	2.5	19
278	High-resolution electron-beam-induced-current study of the defect structure in GaN epilayers. <i>Journal of Physics Condensed Matter</i> , <b>2002</b> , 14, 13285-13290	1.8	19

277	Trapping of gold by nanocavities induced by H <sup>+</sup> or He <sup>++</sup> implantation in float zone and Czochralski grown silicon wafers. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 2806-2812	2.5	17
276	Minority carrier lifetime scan maps applied to iron concentration mapping in silicon wafers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2002</b> , 91-92, 216-219	3.1	16
275	Comparison between the EBIC and XBIC contrasts of dislocations and grain boundaries. <i>Journal of Surface Investigation</i> , <b>2012</b> , 6, 894-896	0.5	15
274	EBIC and CL studies of ELOG GaN films. <i>Superlattices and Microstructures</i> , <b>2009</b> , 45, 308-313	2.8	14
273	Effect of low-energy electron irradiation on the cathodoluminescence of multiple quantum well (MQW) InGaN/GaN structures. <i>Solid State Communications</i> , <b>2011</b> , 151, 208-211	1.6	14
272	Electrical and luminescent properties and deep traps spectra in GaN nanopillar layers prepared by dry etching. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 073112	2.5	14
271	Temperature dependence of electron beam induced current contrast of deformation-induced defects in silicon. <i>Journal of Physics Condensed Matter</i> , <b>2004</b> , 16, S201-S205	1.8	14
270	Dissociation of iron-related centers in Si stimulated by hydrogen. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2000</b> , 71, 268-271	3.1	14
269	Hydrogen interaction with defects in electron-irradiated silicon. <i>Physica B: Condensed Matter</i> , <b>1999</b> , 273-274, 235-238	2.8	14
268	Diffusion length measurements in GaN. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 05FH04	1.4	14
267	Photosensitivity of Ga <sub>2</sub> O <sub>3</sub> Schottky diodes: Effects of deep acceptor traps present before and after neutron irradiation. <i>APL Materials</i> , <b>2020</b> , 8, 111105	5.7	13
266	Pulsed fast reactor neutron irradiation effects in Si doped n-type Ga <sub>2</sub> O <sub>3</sub> . <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 274001	3	13
265	Deep Electron Traps Responsible for Higher Quantum Efficiency in Improved GaN/InGaN Light Emitting Diodes Embedded with SiO <sub>2</sub> Nanoparticles. <i>ECS Journal of Solid State Science and Technology</i> , <b>2016</b> , 5, Q274-Q277	2	13
264	Comparison of the efficiency of <sup>63</sup> Ni beta-radiation detectors made from silicon and wide-gap semiconductors. <i>Journal of Surface Investigation</i> , <b>2014</b> , 8, 843-845	0.5	13
263	Simulation of hydrogen penetration into p-type silicon under wet chemical etching. <i>Semiconductors</i> , <b>2002</b> , 36, 282-285	0.7	13
262	Peculiarities of extended defect system in III-nitrides with different degrees of order of mosaic structure. <i>Physica B: Condensed Matter</i> , <b>2003</b> , 340-342, 462-465	2.8	13
261	SEM/EBIC investigations of extended defect system in GaN epilayers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2005</b> , 2, 1797-1801		13
260	Plasma Stimulated Impurity Redistribution in Silicon. <i>Physica Status Solidi A</i> , <b>1989</b> , 111, 81-88		13

259	Electron traps as major recombination centers in n-GaN films grown by metalorganic chemical vapor deposition. <i>Applied Physics Express</i> , <b>2016</b> , 9, 061002	2.4	13
258	Study of the properties of silicon-based semiconductor converters for betavoltaic cells. <i>Semiconductors</i> , <b>2015</b> , 49, 746-748	0.7	12
257	Simulation of the current induced by <sup>63</sup> Ni beta radiation. <i>Journal of Surface Investigation</i> , <b>2013</b> , 7, 852-855		12
256	Cathodoluminescence and electron beam induced current investigations of stacking faults mechanically introduced in 4H-SiC in the brittle domain. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 084903	2.5	12
255	Electrical properties of undoped GaN films grown by maskless epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 083712	2.5	12
254	Metastable centers in AlGaIn/AlN/GaN heterostructures. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2012</b> , 30, 041209	1.3	12
253	EBIC characterization of light-emitting structures based on GaN. <i>Semiconductors</i> , <b>2007</b> , 41, 491-494	0.7	12
252	Asymmetry of isolated dislocation mobility in Silicon single crystals. <i>Crystal Research and Technology</i> , <b>1984</b> , 19, 295-302	1.3	12
251	Recombination and optical properties of dislocations gliding at room temperature in GaN under applied stress. <i>Journal of Alloys and Compounds</i> , <b>2019</b> , 776, 181-186	5.7	12
250	Effect of low energy electron beam irradiation on Shockley partial dislocations bounding stacking faults introduced by plastic deformation in 4H-SiC in its brittle temperature range. <i>Superlattices and Microstructures</i> , <b>2016</b> , 99, 226-230	2.8	11
249	Crystal structure, vibrational spectroscopy and optical properties of a one-dimensional organic-inorganic hybrid perovskite of [NHCHCH(NH)CH]BiCl. <i>Acta Crystallographica Section B: Structural Science, Crystal Engineering and Materials</i> , <b>2019</b> , 75, 880-886	1.8	11
248	Effect of metal contamination on recombination properties of extended defects in multicrystalline Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2012</b> , 9, 1942-1946		11
247	Structure and recombination properties of extended defects in the dislocation slip plane in silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2007</b> , 4, 3100-3104		11
246	SEM/EBIC investigation of silicon, compensated by zinc during high temperature diffusion annealing. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2008</b> , 19, 277-280	2.1	11
245	Influence of the deformation on the luminescence properties of Si light-emitting diodes. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2005</b> , 2, 1842-1846		11
244	Role of hole trapping by deep acceptors in electron-beam-induced current measurements in EGa <sub>2</sub> O <sub>3</sub> vertical rectifiers. <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 495108	3	11
243	Prediction of betavoltaic battery output parameters based on SEM measurements and Monte Carlo simulation. <i>Applied Radiation and Isotopes</i> , <b>2016</b> , 112, 98-102	1.7	11
242	Deep level defect states in $\alpha$ -Si and e-Ga <sub>2</sub> O <sub>3</sub> crystals and films: Impact on device performance. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2022</b> , 40, 020804	2.9	11

241	Editors' Choice Electrical Properties and Deep Traps in $\text{Ga}_2\text{O}_3:\text{Sn}$ Films Grown on Sapphire by Halide Vapor Phase Epitaxy. <i>ECS Journal of Solid State Science and Technology</i> , <b>2020</b> , 9, 045003	2	10
240	Electrical, optical, and structural properties of GaN films prepared by hydride vapor phase epitaxy. <i>Journal of Alloys and Compounds</i> , <b>2014</b> , 617, 200-206	5.7	10
239	Comment on Carrier recombination near threading dislocations in GaN epilayers by low voltage cathodoluminescence [Appl. Phys. Lett. 89, 161905 (2006)]. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 166101	3.4	10
238	Two channels of non-radiative recombination in InGaN/GaN LEDs. <i>Physica B: Condensed Matter</i> , <b>2009</b> , 404, 4896-4898	2.8	10
237	Dislocation-Point Defect Interaction Effect on Local Electrical Properties of Semiconductors. <i>Journal De Physique III</i> , <b>1997</b> , 7, 2293-2307		10
236	Oxygen Effect on Electrical and Optical Properties of Dislocations in Silicon. <i>Physica Status Solidi A</i> , <b>1999</b> , 171, 341-346		10
235	Apparatus Electron beam microtomography in SEM. <i>Physica Status Solidi A</i> , <b>1995</b> , 150, 211-219		10
234	Heterostructure optimization for increasing LED efficiency. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 05FJ13	1.4	10
233	Properties of nanopillar structures prepared by dry etching of undoped GaN grown by maskless epitaxial overgrowth. <i>Journal of Alloys and Compounds</i> , <b>2013</b> , 554, 258-263	5.7	9
232	Calculating the extended defect contrast for the X-ray-beam-induced current method. <i>Technical Physics Letters</i> , <b>2012</b> , 38, 913-916	0.7	9
231	Capacitance-voltage and admittance investigations of InGaN/GaN MQW LEDs: frequency dependence. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2013</b> , 10, 338-341		9
230	Study of the effect of irradiation with the SEM electron beam on cathodoluminescence and the induced current in InGaN/GaN structures with multiple quantum wells. <i>Journal of Surface Investigation</i> , <b>2011</b> , 5, 945-948	0.5	9
229	Effect of low energy electron irradiation on optical properties of InGaN/GaN light emitting structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 1265-1268		9
228	Electrical properties of dislocation trails in n-Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2007</b> , 4, 3105-3109		9
227	Nitrogen effect on self-interstitial generation in Czochralski silicon revealed by gold diffusion experiments. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 3642-3644	2.5	9
226	Electrical Properties and Defect Structure of Plastically Deformed Silicon Crystals Doped with Gold. <i>Physica Status Solidi A</i> , <b>1987</b> , 102, 687-695		9
225	Radiation enhanced basal plane dislocation glide in GaN. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 05FM03	1.4	9
224	Development of betavoltaic cell technology production based on microchannel silicon and its electrical parameters evaluation. <i>Applied Radiation and Isotopes</i> , <b>2017</b> , 121, 71-75	1.7	8

223	Neutron doping effects in epitaxially laterally overgrown n-GaN. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 212103-4	3.4	8
222	Impact of thermal annealing on deep-level defects in strained-SiBiGe heterostructure. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 103506	2.5	8
221	Application of Surface Electron Beam Induced Voltage Method for the Contactless Characterization of Semiconductor Structures. <i>Solid State Phenomena</i> , <b>1998</b> , 63-64, 327-332	0.4	8
220	Phosphorus diffusion effect on defect structure of silicon with oxygen precipitates revealed by gold diffusion study. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 2054-2056	3.4	8
219	The Electrical Activity of Dislocation Slip Planes in Semiconductor Crystals. <i>Materials Science Forum</i> , <b>1986</b> , 10-12, 787-790	0.4	8
218	Scanning electron microscopy in submicron structure diagnostics. <i>Vacuum</i> , <b>1988</b> , 38, 1045-1050	3.7	8
217	Experimental estimation of electron-hole pair creation energy in Ga <sub>2</sub> O <sub>3</sub> . <i>Applied Physics Letters</i> , <b>2021</b> , 118, 202106	3.4	8
216	Electrical, Luminescent and Structural Properties of Nanopillar GaN/InGaN Multi-Quantum-Well Structures Prepared by Dry Etching. <i>ECS Journal of Solid State Science and Technology</i> , <b>2016</b> , 5, Q165-Q170	1.7	8
215	Quantum Barrier Growth Temperature Affects Deep Traps Spectra of InGaN Blue Light Emitting Diodes. <i>ECS Journal of Solid State Science and Technology</i> , <b>2018</b> , 7, Q80-Q84	2	7
214	Application of a scanning electron microscope in simulating a beta-emission-induced current. <i>Journal of Surface Investigation</i> , <b>2013</b> , 7, 81-84	0.5	7
213	Low temperature stacking fault nucleation and expansion from stress concentrators in 4H-SiC. <i>Acta Materialia</i> , <b>2017</b> , 139, 155-162	8.4	7
212	Microcathodoluminescence spectra evolution for planar and nanopillar multiquantum-well GaN-based structures as a function of electron irradiation dose. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2014</b> , 32, 011207	1.3	7
211	Frequency and temperature dependences of capacitance-voltage characteristics of InGaN/GaN light-emitting structures with multiple quantum wells. <i>Semiconductors</i> , <b>2011</b> , 45, 221-224	0.7	7
210	Electrical properties of plastically deformed silicon due to its interaction with an iron impurity. <i>Physics of the Solid State</i> , <b>2011</b> , 53, 1240-1243	0.8	7
209	X-ray beam induced current method at the laboratory x-ray source. <i>Review of Scientific Instruments</i> , <b>2011</b> , 82, 093702	1.7	7
208	XBIC Investigation of the Grain Boundaries in Multicrystalline Si on the Laboratory X-Ray Source. <i>Solid State Phenomena</i> , <b>2011</b> , 178-179, 226-229	0.4	7
207	EBIC investigations of GaN layers prepared by epitaxial lateral overgrowth. <i>Journal of Surface Investigation</i> , <b>2008</b> , 2, 688-691	0.5	7
206	Electrical and Optical Properties of Dislocations Generated under Pure Conditions. <i>Solid State Phenomena</i> , <b>2003</b> , 95-96, 453-458	0.4	7

205	Spatial distribution of dislocation-related centers in plastically deformed silicon. <i>Physica Status Solidi A</i> , <b>1991</b> , 127, 67-73		7
204	SEM investigation of semiconductors by the capacitance techniques. <i>Microelectronic Engineering</i> , <b>1990</b> , 12, 179-185	2.5	7
203	The Peculiarities of Deep Level Defect Passivation in Si by Atomic Hydrogen. <i>Physica Status Solidi A</i> , <b>1990</b> , 120, 391-395		7
202	Recombination activity of interfaces in multicrystalline silicon. <i>Semiconductors</i> , <b>2015</b> , 49, 724-728	0.7	6
201	Some new insights into the impact of annealing on single stacking faults in 4H-SiC. <i>Superlattices and Microstructures</i> , <b>2018</b> , 120, 7-14	2.8	6
200	Characterization of Si Convertors of Beta-Radiation in the Scanning Electron Microscope. <i>Solid State Phenomena</i> , <b>2015</b> , 242, 312-315	0.4	6
199	Investigation of electrical and optical properties in semiconductor structures via SEM techniques with high spatial resolution. <i>Journal of Surface Investigation</i> , <b>2012</b> , 6, 887-889	0.5	6
198	Influence of metal impurities on recombination activity of dislocations in multicrystalline silicon. <i>Semiconductors</i> , <b>2013</b> , 47, 232-234	0.7	6
197	Study of dislocation EBIC image width in GaN films and GaN based structures. <i>Journal of Surface Investigation</i> , <b>2009</b> , 3, 58-60	0.5	6
196	Effect of mesoscopic inhomogeneities on the critical current of bulk melt-textured YBCO. <i>Physica C: Superconductivity and Its Applications</i> , <b>2003</b> , 390, 127-133	1.3	6
195	Gold Diffusion as a Tool for Defect Characterization in Si. <i>Solid State Phenomena</i> , <b>2003</b> , 95-96, 495-500	0.4	6
194	Gold and platinum profiles in fast power devices. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2000</b> , 71, 166-170	3.1	6
193	Interaction of gold with dislocations in silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2000</b> , 71, 272-275	3.1	6
192	Possibilities of modulated cathodoluminescence for multilayer structure characterization. <i>Scanning</i> , <b>1993</b> , 15, 31-36	1.6	6
191	The Influence of Thermal Treatment on Thermally Stimulated Depolarization Spectrum of the Electret State in Plastically Deformed Silicon. <i>Physica Status Solidi A</i> , <b>1984</b> , 84, 443-450		6
190	Electrical properties and deep trap spectra in Ga <sub>2</sub> O <sub>3</sub> films grown by halide vapor phase epitaxy on p-type diamond substrates. <i>Journal of Applied Physics</i> , <b>2021</b> , 129, 185701	2.5	6
189	On the nature of photosensitivity gain in Ga <sub>2</sub> O <sub>3</sub> Schottky diode detectors: Effects of hole trapping by deep acceptors. <i>Journal of Alloys and Compounds</i> , <b>2021</b> , 879, 160394	5.7	6
188	Electron beam induced excess carrier concentration. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2017</b> , 14, 1600266		6



187	Spatial Distribution of the Dislocation Trails in Silicon. <i>Solid State Phenomena</i> , <b>2015</b> , 242, 155-159	0.4	5
186	EBIC and LBIC investigations of dislocation trails in Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2015</b> , 12, 1081-1084		5
185	EBIC investigations of dislocations in ELOG GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2015</b> , 12, 1132-1135		5
184	Increase in the diffusion length of minority carriers in Al <sub>x</sub> Ga <sub>1-x</sub> N alloys (x = 0.1) fabricated by ammonia molecular beam epitaxy. <i>Semiconductors</i> , <b>2015</b> , 49, 1285-1289	0.7	5
183	Analysis of the temperature dependence of the capacitance-voltage characteristics of InGaN/GaN multiple quantum well light-emitting structures. <i>Semiconductors</i> , <b>2013</b> , 47, 162-168	0.7	5
182	EBIC investigation of InGaN/GaN multiple quantum well structures irradiated with low energy electrons. <i>Journal of Physics: Conference Series</i> , <b>2011</b> , 281, 012013	0.3	5
181	Effect of the silicon doping level and features of nanostructural arrangement on decrease in external quantum efficiency in InGaN/GaN light-emitting diodes with increasing current. <i>Semiconductors</i> , <b>2011</b> , 45, 415-421	0.7	5
180	Characterization of silicon ribbon by the SEM methods. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 1384-1387		5
179	Cathodoluminescence study of individual ZnO nanorods. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 1403-1406		5
178	Electrical properties and deep traps spectra in undoped M-plane GaN films prepared by standard MOCVD and by selective lateral overgrowth. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 2923-2925	1.6	5
177	EBIC characterization of strained Si/SiGe heterostructures. <i>Semiconductors</i> , <b>2007</b> , 41, 402-406	0.7	5
176	Electroluminescent properties of strained p-Si LEDs. <i>Semiconductors</i> , <b>2005</b> , 39, 1229	0.7	5
175	Oxygen precipitate precursors and low temperature gettering processes. II. DLTS analysis of deep levels associated to oxide precipitates. <i>Materials Science in Semiconductor Processing</i> , <b>1999</b> , 2, 69-74	4.3	5
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